



SEMITOP® 2

Bridge Rectifier

SK 55 D

Preliminary Data

Features

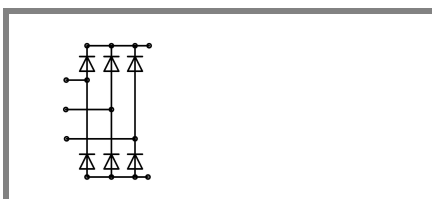
- Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB)
- Up to 1600V reverse voltage
- High surge currents
- Glass passivated diodes chips
- UL recognized, file no. E 63 532

Typical Applications

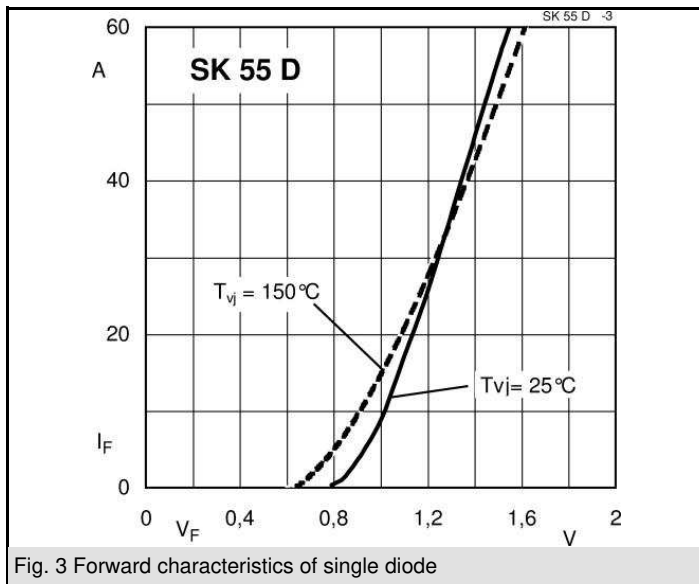
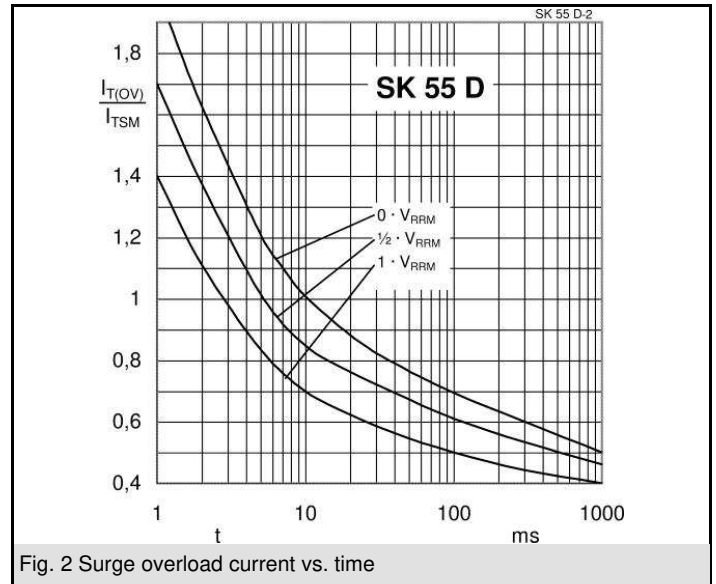
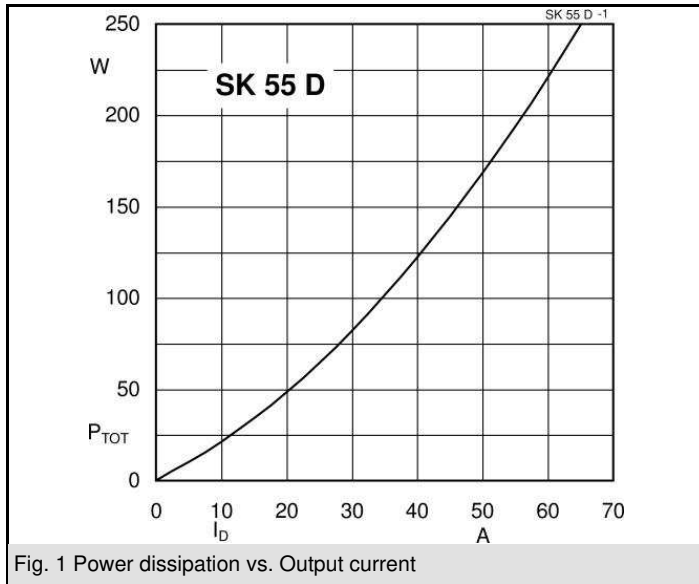
- Input rectifier for power supplies
- Rectifier

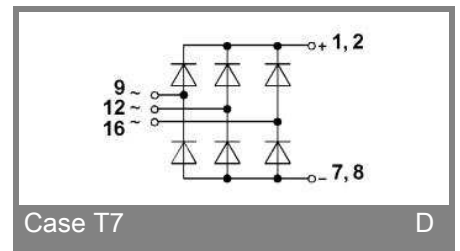
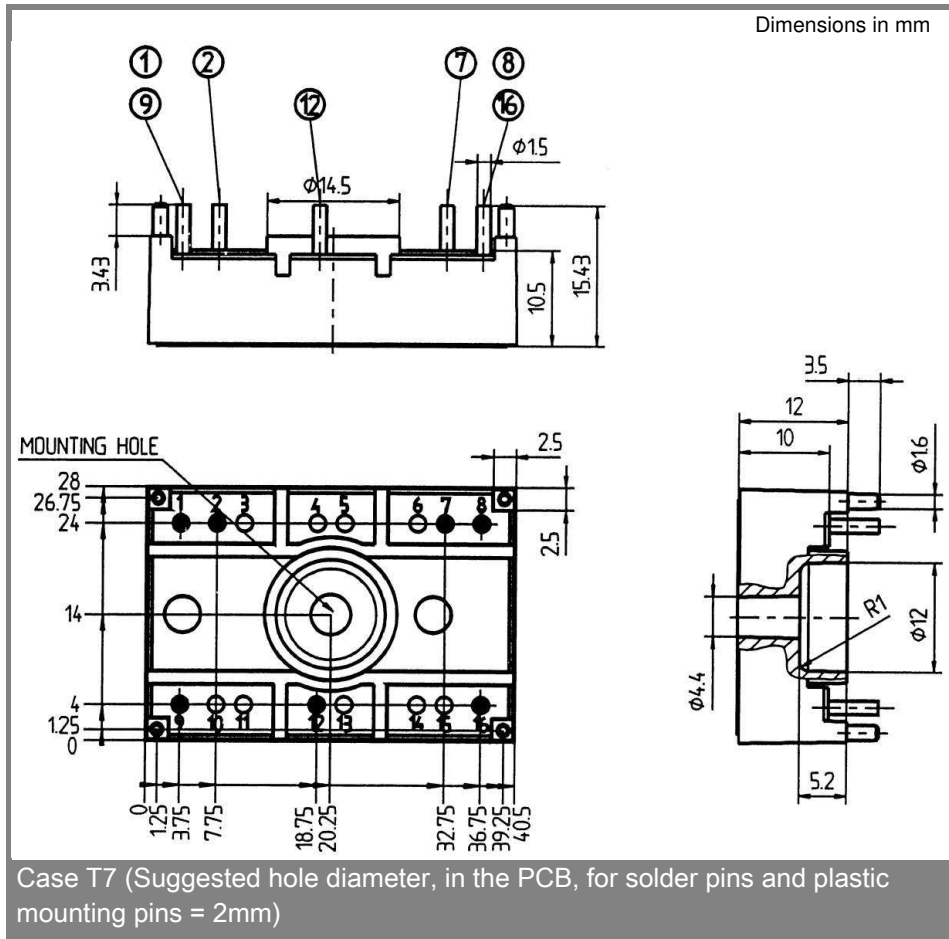
V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 55 \text{ A (full conduction)}$ ($T_s = 80 \text{ °C}$)
800	800	SK 55 D 08
1200	1200	SK 55 D 12
1600	1600	SK 55 D 16

Symbol	Conditions	Values	Units
I_D	$T_s = 80 \text{ °C}$	55	A
I_D	$T_s = 100 \text{ °C}$	45	A
I_{FSM}	$T_{vj} = 25 \text{ °C}; 10 \text{ ms}$	220	A
	$T_{vj} = 150 \text{ °C}; 10 \text{ ms}$	200	A
i^2t	$T_{vj} = 25 \text{ °C}; 8,3...10 \text{ ms}$	242	A ² s
	$T_{vj} = 150 \text{ °C}; 8,3...10 \text{ ms}$	200	A ² s
V_F	$T_{vj} = 25 \text{ °C}; I_F = 25 \text{ A}$	max. 1,25	V
$V_{(TO)}$	$T_{vj} = 150 \text{ °C}$	max. 0,8	V
r_T	$T_{vj} = 150 \text{ °C}$	max. 13	mΩ
I_{RD}	$T_{vj} = 150 \text{ °C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$	max. 4	mA
$R_{th(j-s)}$	per diode	2,15	K/W
	per module	0,36	K/W
T_{solder}	terminals, 10s	260	°C
T_{vj}		-40...+150	°C
T_{stg}		-40...+125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 (2500)	V
M_s	mounting torque to heatsink	2	Nm
M_t			
m	approx. weight	19	g
Case	SEMITOP® 2	T 7	



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